

/ Descriptions

TO-126F NPN Silicon NPN transistor in a TO-126F Plastic Package.

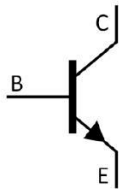
/ Features

High breakdown voltage, small reverse transfer capacitance and excellent high frequency characteristic.

/ Applications

CRT
Ultrahigh-definition CRT display, video output applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	C	D	E	F
h_{FE} Range	40~80	60~120	100~200	160~320

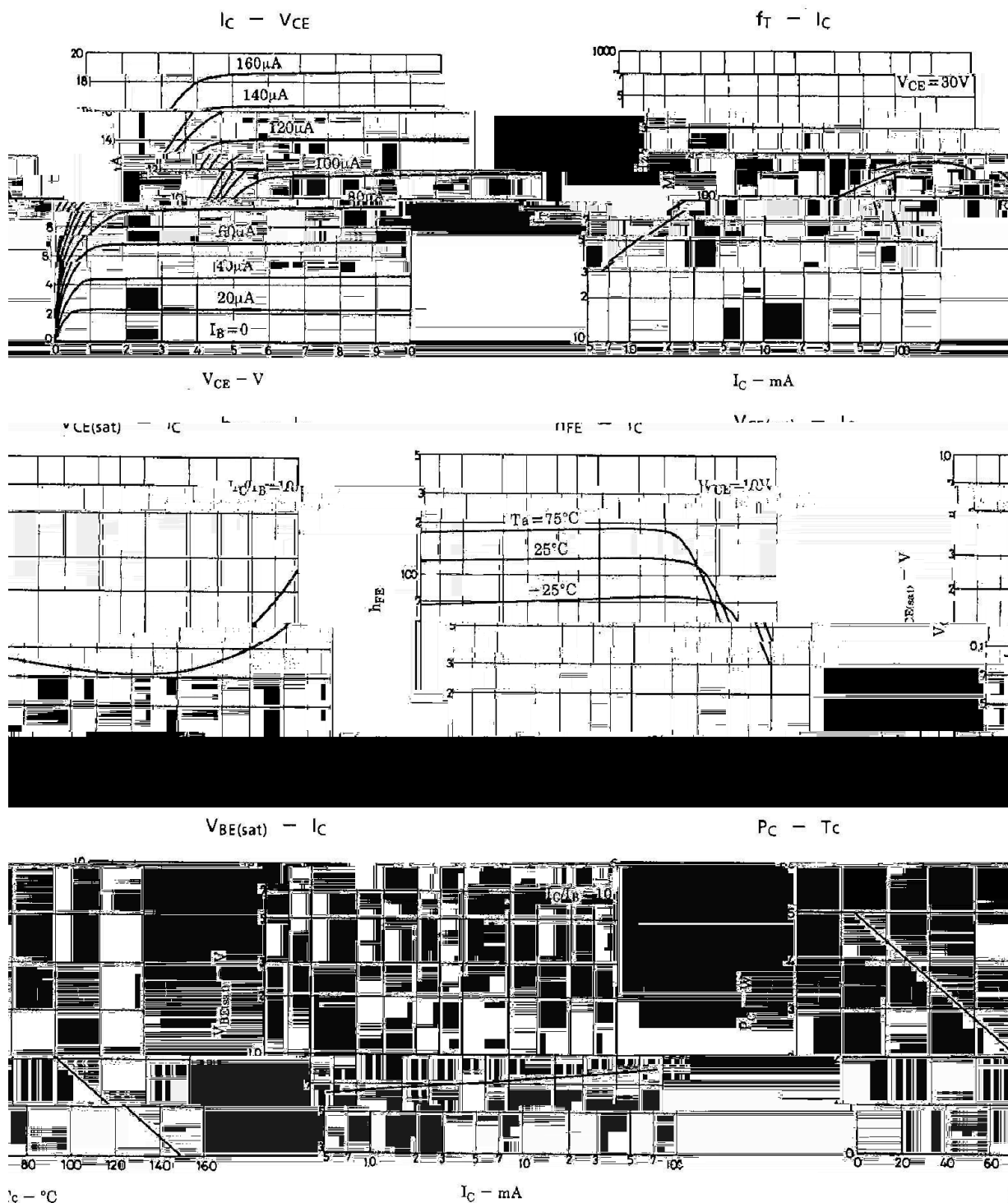
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	200	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Current – Continuous(Pulse)	I_{CP}	200	mA
Collector Power Dissipation	P_C	1.2	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

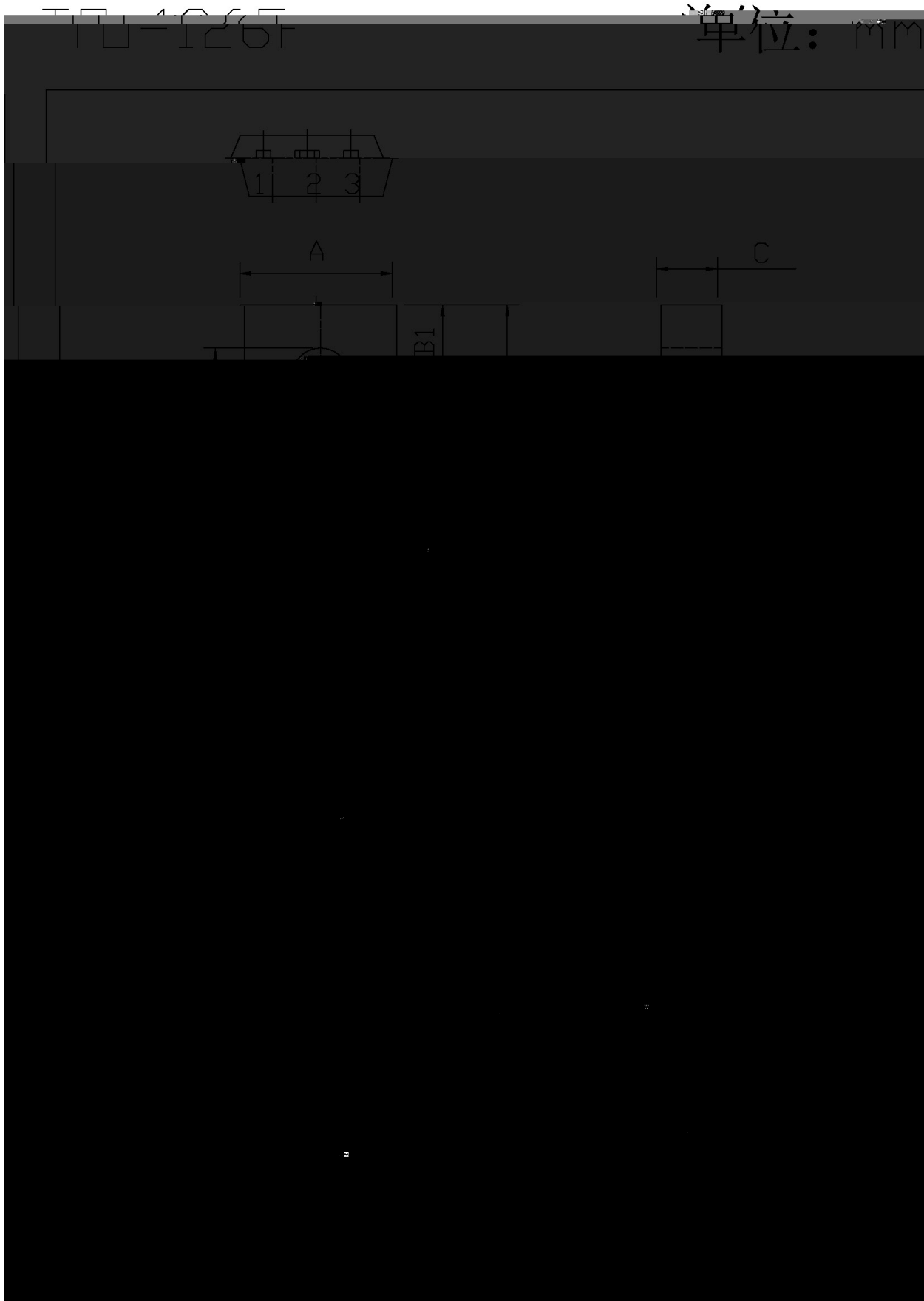
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=10\mu A$ $I_E=0$	200			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $R_{BE}=\infty$	200			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10\mu A$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=150V$ $I_E=0$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=4.0V$ $I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=10V$ $I_C=10mA$	40		320	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=20mA$ $I_B=2.0mA$			0.6	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=20mA$ $I_B=2.0mA$			1.0	V
Transition Frequency	f_T	$V_{CE}=30V$ $I_C=10mA$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=30V$ $f=1.0MHz$		2.6		pF
Reverse Transfer Capacitance	C_{re}	$V_{CB}=30V$ $f=1.0MHz$		1.7		pF

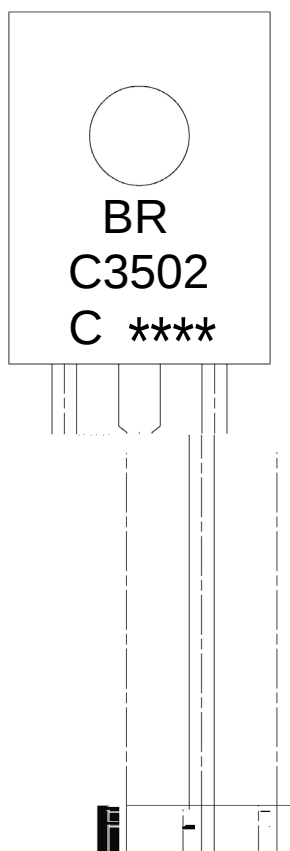
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

C3502

C

h_{FE}

Note:

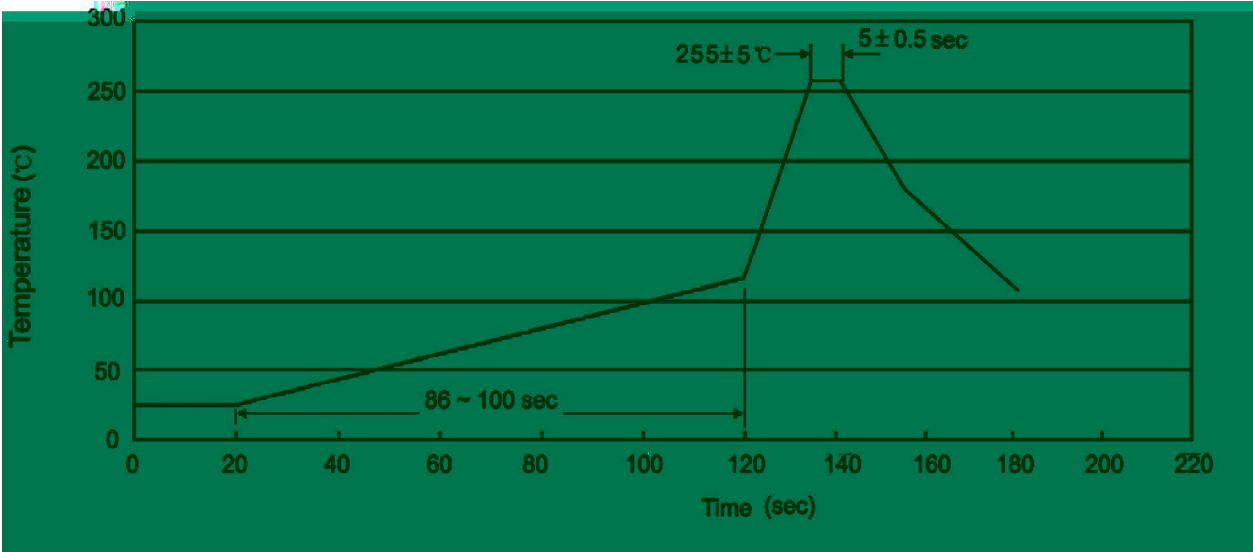
BR: Company Code

C3502: Product Type.

C h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255±5

, Duration:5±0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-126/F	500	6	3,000	5	15,000	135×190	237×172×102	560×245×195

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		